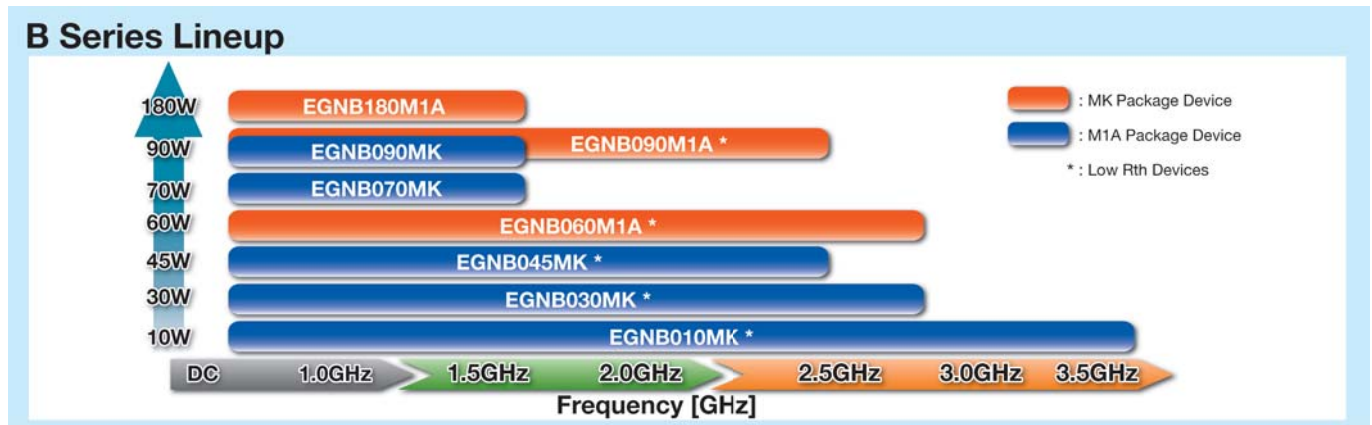
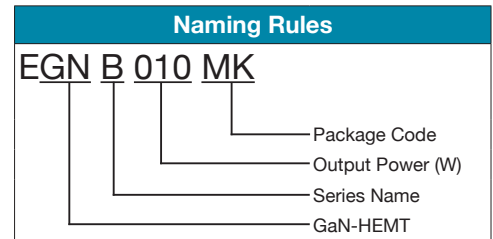


# GaN HEMTs (High Electron Mobility Transistors)

## For General Purpose (B series)

### Features

- Higher Load Impedance: 5Ω to 20Ω (Easy Match, Wide Band)
- High Operating Voltage: 50V
- High Power: Up to 180W P3dB
- High Efficiency
- Low Thermal Resistance (Rth)



## Specifications

Part Number	Frequency (GHz)	P3dB Typ. (dBm)	GL Typ. (dB)	$\eta$ @P3dB Typ. (%)	IDS (DC) (mA)	Rth Typ. (°C/W)	Outline/Package Code
EGNB010MK	3.5	41.0	13.0	60	100	4.5	MK
EGNB030MK	2.7	46.5	13.0	60	200	2.0	
EGNB045MK	2.2	47.5	13.0	60	250	1.4	
EGNB070MK	0.9	49.5	18.0	70	400	1.5	
EGNB090MK	0.9	51.0	18.0	70	500	1.2	
EGNB060M1A	2.7	49.0	12.0	55	400	1.1	M1A
EGNB090M1A	2.2	50.5	12.0	55	500	0.75	
EGNB180M1A	0.9	53.5	17.5	65	1000	0.65	

Note: Tc (op)=+25°C

## For General Purpose (E series)

### Features

- Higher Gain: GL=16dB @f=2.7GHz, 30W Device
- High Operating Voltage: 50V
- Low Thermal Resistance (Rth)

## Specifications

Part Number	Frequency (GHz)	Psat Typ. (dBm)	GL Typ. (dB)	$\eta$ @Psat Typ. (%)	IDS (DC) (mA)	Rth Typ. (°C/W)	Outline/Package Code
SGNE010MK*	3.5	40.5	16.0	55	100	4.5	MK
SGNE030MK*	2.7	46.5	16.0	55	200	2.0	
SGNE045MK*	2.2	47.5	15.0	55	250	1.4	
SGNE070MK*	0.9	49.5	20.0	65	400	1.5	
SGNE090MK*	0.9	51.0	20.0	65	500	1.2	

\* Under development, Sample Available

Note: Tc=+25°C